2SK3207

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

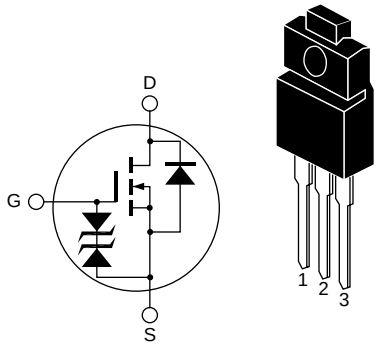
ADE-208-758A(Z)
Target Specification 2nd. Edition
Feb 1999

Features

- Low on-resistance
  R_{DS} = 70 mΩ typ.
- High speed switching
- 4V gate drive device can be driven from 5V source

Outline

TO–220FM



1. Gate
2. Drain
3. Source

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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	150	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	18	A
Drain peak current	$I_{D(pulse)}$*[1]	72	A
Body-drain diode reverse drain current	I_{DR}	18	A
Avalanche current	I_{AP}*[3]	18	A
Avalanche energy	E_{AR}*[3]	24	mJ
Channel dissipation	Pch*[2]	35	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Note: 1. PW ≤ 10μs, duty cycle ≤ 1 %
2. Value at Tc = 25°C
3. Value at Tch = 25°C, Rg ≥ 50Ω

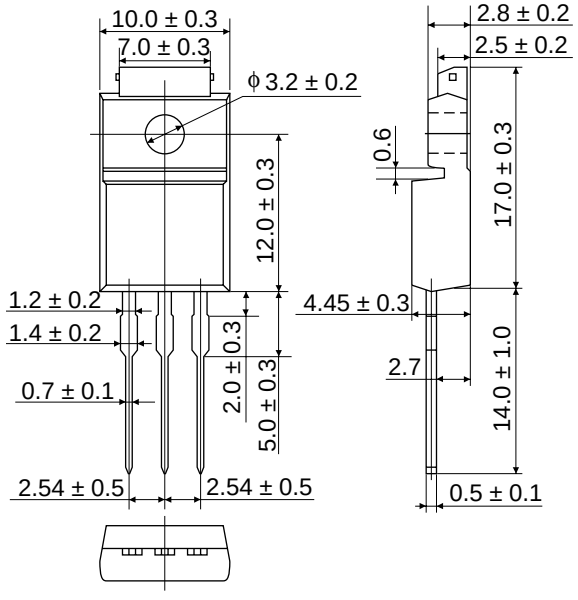
Electrical Characteristics (Ta = 25°C)

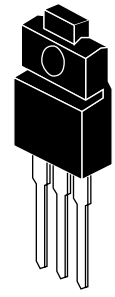
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	150	—	—	V	I_D = 10mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±10	µA	V_{GS} = ±16V, V_{DS} = 0
Zero gate voltege drain current	I_{DSS}	—	—	10	µA	V_{DS} = 150 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	I_D = 1mA, V_{DS} = 10V
Static drain to source on state resistance	$R_{DS(on)}$	—	70	90	mΩ	I_D = 9A, V_{GS} = 10V*[4]
	$R_{DS(on)}$	—	85	120	mΩ	I_D = 9A, V_{GS} = 4V*[4]
Forward transfer admittance	$\|y_{fs}\|$	11	18	—	S	I_D = 9A, V_{DS} = 10V*[4]
Input capacitance	Ciss	—	1100	—	pF	V_{DS} = 10V
Output capacitance	Coss	—	350	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	170	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	15	—	ns	I_D = 9A, V_{GS} = 10V
Rise time	t_r	—	110	—	ns	R_L = 3.33Ω
Turn-off delay time	$t_{d(off)}$	—	270	—	ns	
Fall time	t_f	—	130	—	ns	
Body–drain diode forward voltage	V_{DF}	—	0.9	—	V	I_F = 18A, V_{GS} = 0
Body–drain diode reverse recovery time	t_{rr}	—	150	—	ns	I_F = 18A, V_{GS} = 0 diF/ dt = 50A/µs

Note: 4. Pulse test

Package Dimensions

Unit: mm





Hitachi Code	TO–220FM
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